

Data Sheet June 2000 File Number 4869.1

# Radiation Hardened 8-Channel Source Driver



The Star\*Power Radiation Hardened IS-2981RH is a monolithic device designed for use in high-side switching applications that benefit

from separate grounds for the logic and loads. The device has a 5V to 80V operating supply voltage range and is capable of sourcing -200mA continuously from each output. The outputs are controlled by active-high inputs and may be paralleled to increase the drive current. Output clamp diodes prevent device damage, when switching inductive loads.

Constructed with the Intersil bonded wafer, dielectrically isolated HVTDLM process, these single event latch-up immune devices have been specifically designed to provide highly reliable performance in harsh radiation environments. They are fully guaranteed for 100krad(Si) total dose performance through wafer-by-wafer radiation testing, and are production tested over the full military temperature range.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

Detailed Electrical Specifications for these devices are contained in SMD 5962-00520. A "hot-link" is provided on our homepage for downloading. www.intersil.com/spacedefense/space.htm

# Ordering Information

ORDERING NUMBER	INTERNAL MKT. NUMBER	TEMP. RANGE (°C)
5962R0052001VVC	IS1-2981RH-Q	-55 to 125
5962R0052001QVC	IS1-2981RH-8	-55 to 125
IS1-2981RH/Proto	IS1-2981RH/Proto	-55 to 125

#### **Features**

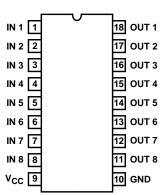
- Electrically Screened to SMD # 5962-00520
- · QML Qualified Per MIL-PRF-38535 Requirements
- · Radiation Environment
- Turn-off Delay Time .......11µs (Max)
- Output Clamp Diode, V<sub>F</sub> . . . . . . . . -1.75V (Max)

# **Applications**

- · Drivers for Various Loads
  - Relays, Solenoids and Motors
- Reliable Replacement of Discrete Solutions
- Interfacing Between Low-Level Logic and High-Current Loads

## **Pinout**

IS1-2981RH-Q (CDIP2-T18, SBDIP) TOP VIEW



## Die Characteristics

### **DIE DIMENSIONS:**

 $2667\mu m$  x  $5131\mu m$  (105 mils x 202 mils) Thickness:  $483\mu m \pm 25.4\mu m$  (19 mils  $\pm$  1 mil)

## **INTERFACE MATERIALS**

#### Glassivation

Type: Nitride ( $Si_3N_4$ ) over Silox ( $SiO_2$ ) Nitride Thickness:  $4.0k\mathring{A} \pm 1.0k\mathring{A}$ Silox Thickness:  $12.0k\mathring{A} \pm 4.0k\mathring{A}$ 

#### Metallization

Top Metal 2: Ti/AlCu Thickness: 1.6μm ± 0.02μm

Metal 1: Ti/AlCu

Thickness:  $0.8\mu m \pm 0.01\mu m$ 

#### **Substrate**

HVTDLM, Bonded Wafer, Dielectric Isolation

#### **Backside Finish**

Silicon

## **ASSEMBLY RELATED INFORMATION**

#### **Substrate Potential**

Must be tied to GND.

#### ADDITIONAL INFORMATION

## **Worst Case Current Density**

 $<1.0 \times 10^5 \text{ A/cm}^2$ 

#### **Transistor Count**

68

# Metallization Mask Layout

# 

## NOTES:

- 1. Pad numbers correspond to package pin functions.
- 2. Bond to all four pad 9 locations for V<sub>CC</sub> current sharing purposes.
- 3. Bond to both pad 10 locations for GND current sharing purposes.
- 4. Pad 10A is not used in die applications.
- 5. Die backside must be connected to GND.

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# IS-2981RH

Printer Friendly Version

## Rad-Hard 8-Channel Source Driver



## Ordering Information

# RoHS/Pb-Free/Green Device

Part No.	Design- In Status		Package	MSL	SMD	Price US \$	
IS0-2981RH- Q	Active	-	18 Ld Die (Military Visual)	N/A	-	Contact Us	Buy
IS1-2981RH- 8 <b>®</b>	Active	-	18 Ld SBDIP	N/A	5962R0052001QVC	Contact Us	Buy
IS1-2981RH- Q	Active	-	18 Ld SBDIP	N/A	5962R0052001VVC	Contact Us	Buy

The price listed is the manufacturer's suggested retail price for quantities between 100 and 999 units. However, prices in today's market are fluid and may change without notice.

MSL = Moisture Sensitivity Level - per IPC/JEDEC J-STD-020

**SMD** = Standard Microcircuit Drawing

# Description

The Star\*Power Radiation Hardened IS-2981RH is a monolithic device designed for use in high-side switching applications that benefit from separate grounds for the logic and loads. The device has a 5V to 80V operating supply voltage range and is capable of sourcing -200mA continuously from each output. The outputs are controlled by active-high inputs and may be paralleled to increase the drive current. Output clamp diodes prevent device damage, when switching inductive loads.

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# Key Features

- Electrically Screened to SMD # 5962-00520
- QML Qualified Per MIL-PRF-38535 Requirements
- Radiation Environment
- Single Event Latch-up Immune DI Process
- Total Dose 1 x 10<sup>5</sup> rad(Si) (Max)
- Input Voltage Range 0.0V to V<sub>CC</sub> (20V Max)
- Supply Voltage Range 5V to 80V
- Turn-on Delay Time 2µs (Max)
- Turn-off Delay Time 11µs (Max)
- Output Clamp Diode, VF -1.75V (Max)

#### **Related Documentation**

Datasheet(s):

• Radiation Hardened 8-Channel Source Driver

Military SMD(s):

• SMD for IS-2981RH

The Technical Homepage:

• Military/Space ICs

PT Parametric Data

RH Level

100

Application Block Diagrams

• Satellite Power Management

# **Applications**

- Drivers for Various Loads
- Relays, Solenoids and Motors
- Reliable Replacement of Discrete Solutions
- Interfacing Between Low-Level Logic and High-Current Loads

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